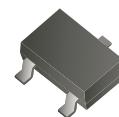


General Purpose Transistor

Comchip
SMD Diode Specialist

AFMMT491-HF (NPN)

RoHS Device
Halogen Free



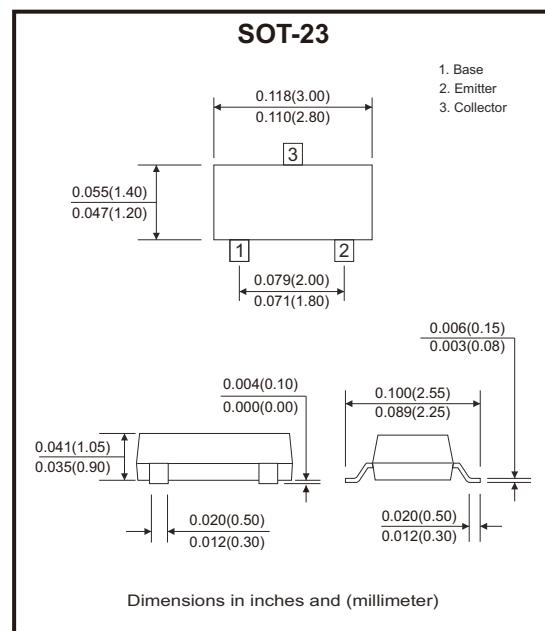
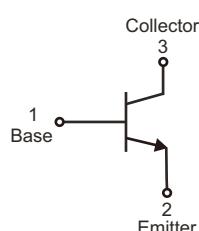
Features

- Low equivalent on-resistance.
- Surface mount package ideally suited for automatic insertion.
- AEC-Q101 Qualified.

Mechanical data

- Case: SOT-23, molded plastic.
- Terminals: Solderable per MIL-STD-750, method 2026.
- Mounting position: Any.

Circuit Diagram



Maximum Ratings (at $T_J=25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Value	Unit
Collector-base voltage	V_{CBO}	80	V
Collector-emitter voltage	V_{CEO}	60	V
Emitter-base voltage	V_{EBO}	5	V
Collector continuous current	I_C	1	A
Peak pulse current	I_{CM}	2	A
Collector power dissipation	P_C	250	mW
Thermal resistance from junction to ambient	$R_{\theta JA}$	500	°C/W
Operation junction and storage temperature range	T_J, T_{STG}	-55 to +150	°C

Electrical Characteristics (at $T_J=25^\circ\text{C}$ unless otherwise noted)

Parameter	Conditions	Symbol	Min	Typ	Max	Unit
Collector-base breakdown voltage	$I_C = 100\mu\text{A}, I_E = 0\text{A}$	$V_{(\text{BR})\text{CBO}}$	80			V
Collector-emitter breakdown voltage (Note 1)	$I_C = 10\text{mA}, I_B = 0\text{A}$	$V_{(\text{BR})\text{CEO}}$	60			V
Emitter-base breakdown voltage	$I_E = 100\mu\text{A}, I_C = 0\text{A}$	$V_{(\text{BR})\text{EBO}}$	5			V
Collector cut-off current	$V_{CB} = 60\text{V}, I_E = 0\text{A}$	I_{CBO}			0.1	μA
Emitter-base cut-off current	$V_{EB} = 4\text{V}, I_C = 0\text{A}$	I_{EBO}			0.1	μA
DC current gain (Note 1)	$V_{CE} = 5\text{V}, I_C = 1\text{mA}$	$h_{FE(1)}$	100			
	$V_{CE} = 5\text{V}, I_C = 500\text{mA}$	$h_{FE(2)}$	100		300	
	$V_{CE} = 5\text{V}, I_C = 1\text{A}$	$h_{FE(3)}$	80			
	$V_{CE} = 5\text{V}, I_C = 2\text{A}$	$h_{FE(4)}$	30			
Collector-emitter saturation voltage (Note 1)	$I_C = 500\text{mA}, I_B = 50\text{mA}$	$V_{CE(\text{sat}) 1}$			0.25	V
	$I_C = 1\text{A}, I_B = 100\text{mA}$	$V_{CE(\text{sat}) 2}$			0.5	V
Base-emitter saturation voltage (Note 1)	$I_C = 1\text{A}, I_B = 100\text{mA}$	$V_{BE(\text{sat})}$			1.1	V
Base-emitter voltage (Note 1)	$V_{CE} = 5\text{V}, I_C = 1\text{A}$	V_{BE}			1	V
Transition frequency	$V_{CE} = 10\text{V}, I_C = 50\text{mA}, f = 100\text{MHz}$	f_T	150			MHz
Collector output capacitance	$V_{CB} = 10\text{V}, f = 1\text{MHz}$	C_{ob}			10	pF

Note: 1. Measured under pulse conditions, pulse width = 300μs, duty cycle ≤ 2%.

Typical Rating and Characteristic Curves (AFMMT491-HF)

Fig.1 - Static Characteristic

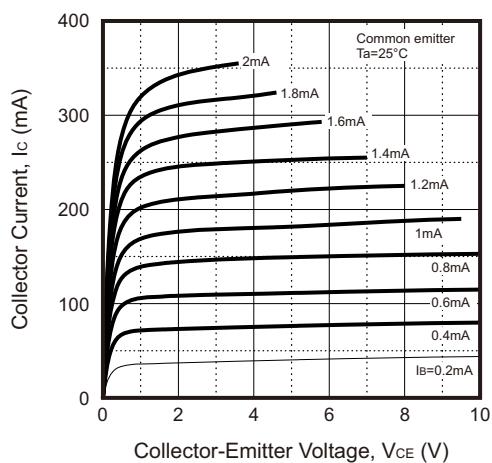
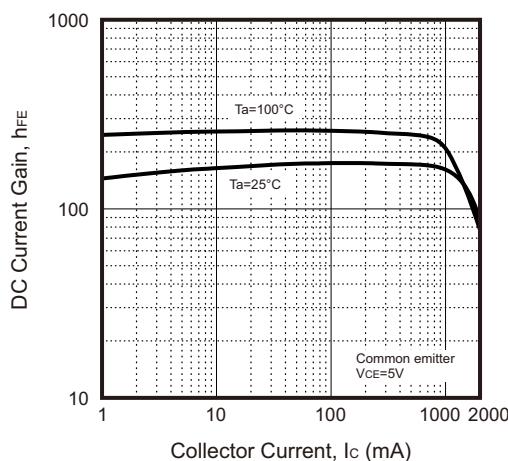
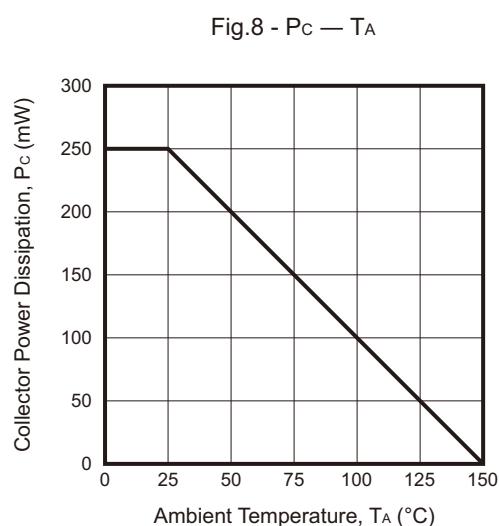
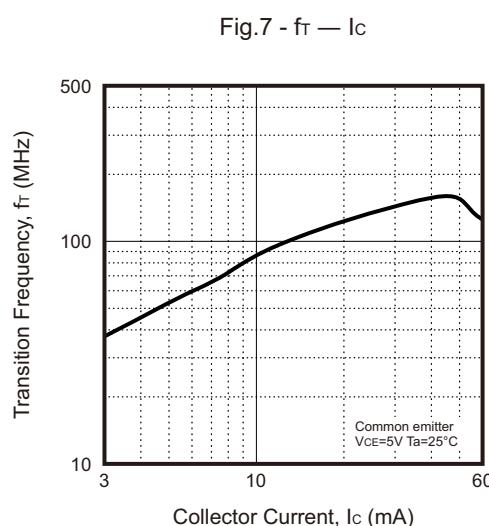
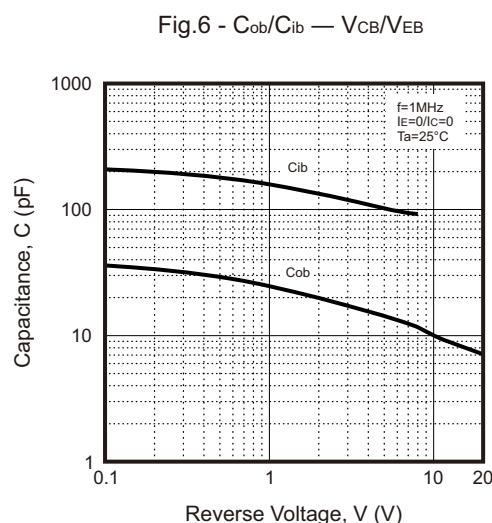
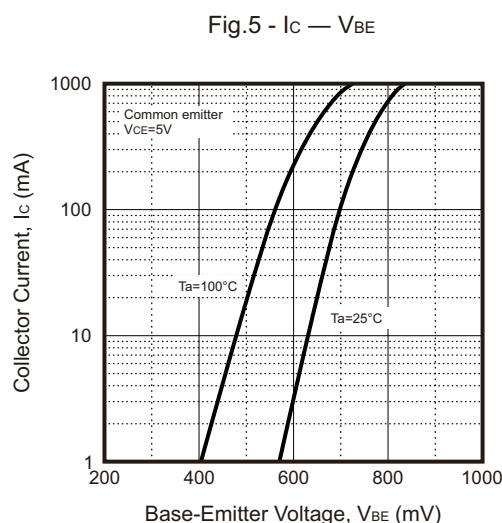
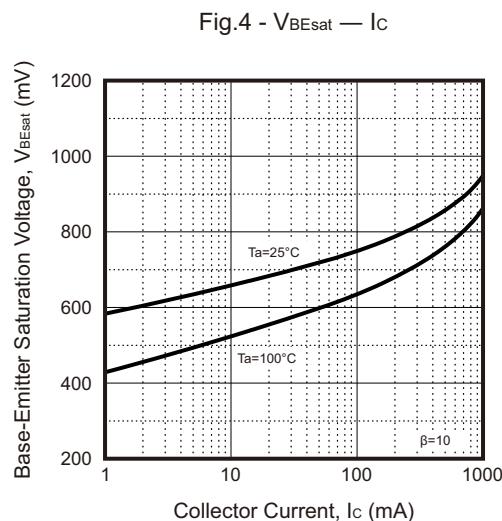
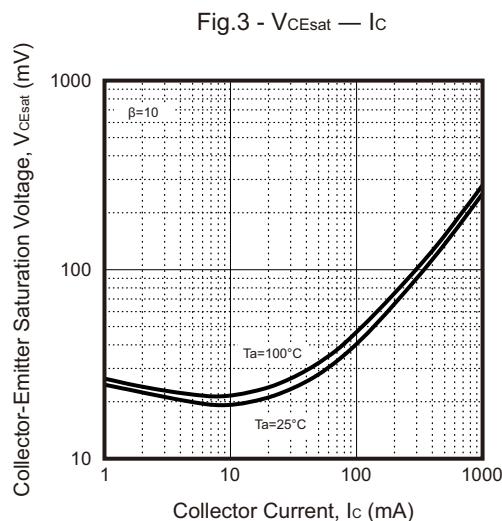


Fig.2 - h_{FE} — I_C

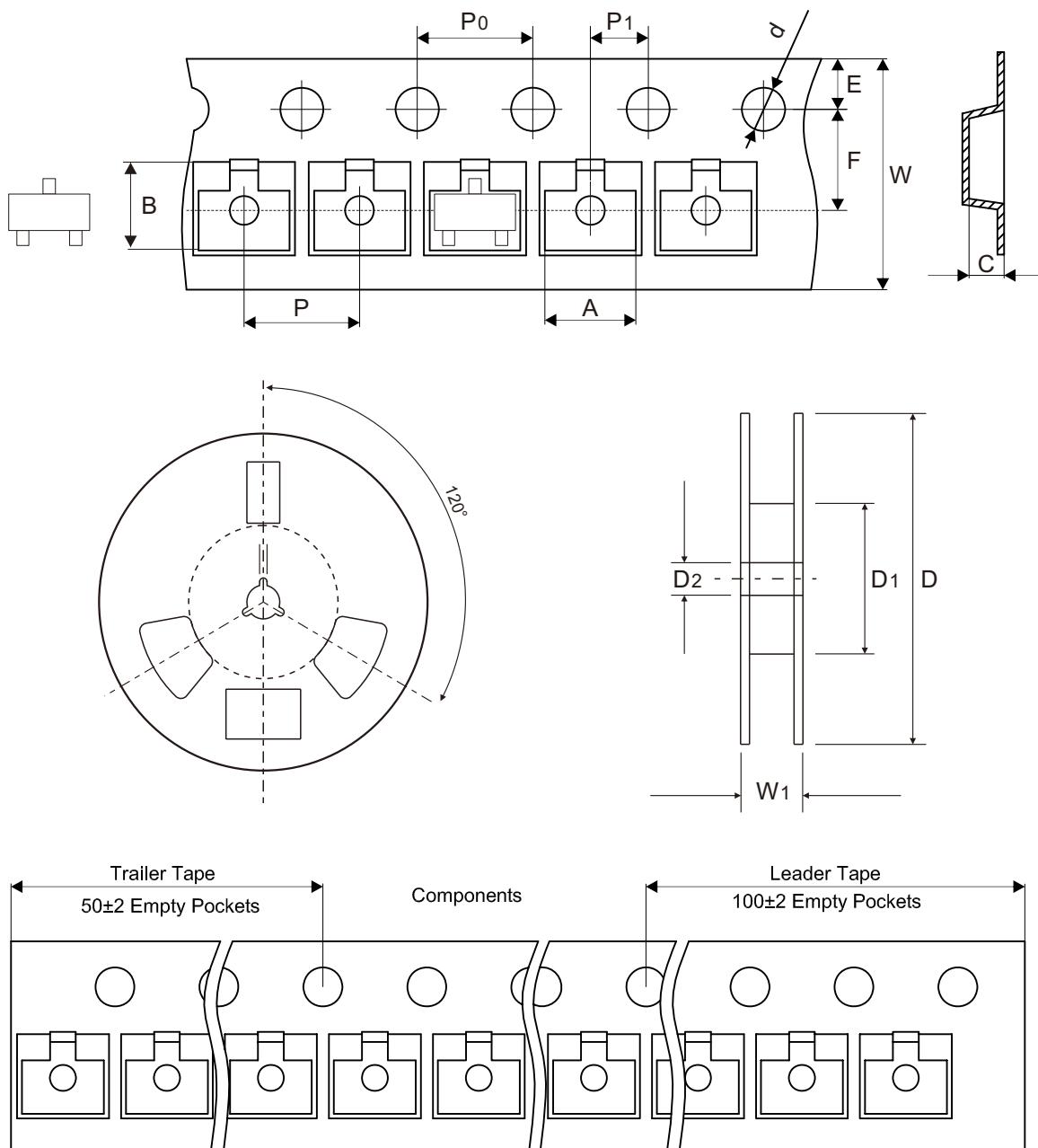


General Purpose Transistor

Typical Rating and Characteristic Curves (AFMMT491-HF)



Reel Taping Specification



SOT-23	SYMBOL	A	B	C	d	D	D1	D2
	(mm)	3.15 ± 0.10	2.77 ± 0.10	1.22 ± 0.10	$1.50 + 0.10$ $- 0.00$	178.00 ± 1.00	54.40 ± 0.40	13.00 ± 0.20
	(inch)	0.124 ± 0.004	0.109 ± 0.004	0.048 ± 0.004	$0.059 + 0.004$ $- 0.000$	7.008 ± 0.039	2.142 ± 0.016	0.512 ± 0.008

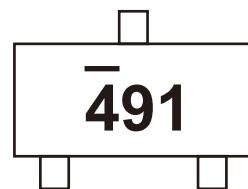
SOT-23	SYMBOL	E	F	P	P0	P1	W	W1
	(mm)	1.75 ± 0.10	3.50 ± 0.05	4.00 ± 0.10	4.00 ± 0.10	2.00 ± 0.05	$8.00 + 0.30$ $- 0.10$	12.10 ± 1.00
	(inch)	0.069 ± 0.004	0.138 ± 0.002	0.157 ± 0.004	0.157 ± 0.004	0.079 ± 0.002	$0.315 + 0.012$ $- 0.004$	0.476 ± 0.039

General Purpose Transistor

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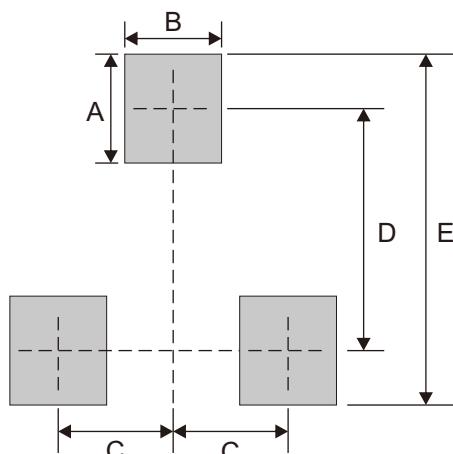
Marking Code

Part Number	Marking Code
AFMMT491-HF	491



Suggested P.C.B. PAD Layout

SIZE	SOT-23	
	(mm)	(inch)
A	0.90	0.035
B	0.80	0.031
C	0.95	0.037
D	2.00	0.079
E	2.90	0.114



Standard Packaging

Case Type	REEL PACK	
	REEL (pcs)	Reel Size (inch)
SOT-23	3,000	7